



SHENZHEN LONG JING MICRO-ELECTRONICS CO., LTD.

SOT-89 Plastic-Encapsulate Transistors

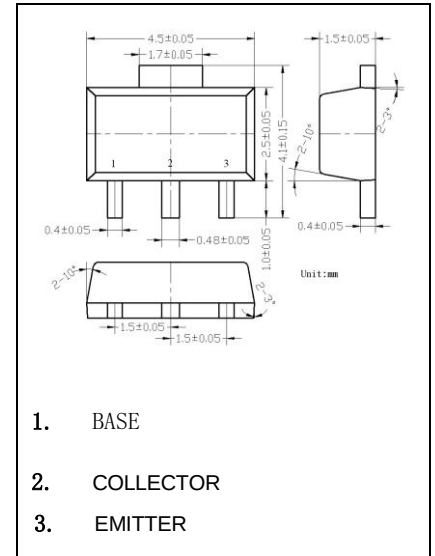
2SB1132 TRANSISTOR (PNP)

Features:

Compliments 2SD1664

MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-32	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_{C}	Collector Current-Continuous	-1	A
I_{CP}	Collector Current -Pulsed	-2	A
P_{C}	Collector Power Dissipation	500	mW
T_{j}	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55-150	$^{\circ}\text{C}$



ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{\text{(BR)CBO}}$	$I_{\text{C}} = -50\mu\text{A}, I_{\text{E}} = 0$	-40			V
Collector-emitter breakdown voltage *	$V_{\text{(BR)CEO}}$	$I_{\text{C}} = -1\text{mA}, I_{\text{B}} = 0$	-32			V
Emitter-base breakdown voltage	$V_{\text{(BR)EBO}}$	$I_{\text{E}} = -50\mu\text{A}, I_{\text{C}} = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{\text{CB}} = -20\text{V}, I_{\text{E}} = 0$			-0.5	μA
Emitter cut-off current	I_{EBO}	$V_{\text{EB}} = -4\text{V}, I_{\text{C}} = 0$			-0.5	μA
DC current gain	$h_{\text{FE(1)}}$	$V_{\text{CE}} = -3\text{V}, I_{\text{C}} = -100\text{mA}$	82		390	
Collector-emitter saturation voltage	$V_{\text{CE(sat)}}$	$I_{\text{C}} = -500\text{mA}, I_{\text{B}} = -50\text{mA}$		-0.2	-0.5	V
Transition frequency	f_{T}	$V_{\text{CE}} = -5\text{V}, I_{\text{C}} = -50\text{mA}, f = 30\text{MHZ}$		150		MHZ
Collector output capacitance	C_{ob}	$V_{\text{CB}} = -10\text{V}, I_{\text{E}} = 0, f = 1\text{MHZ}$		20	30	PF

CLASSIFICATION OF h_{FE}

Rank	P	Q	R
Range	82-180	120-270	180-390
Marking	BAP	BAQ	BAR

Typical Characteristics

2SB1132

